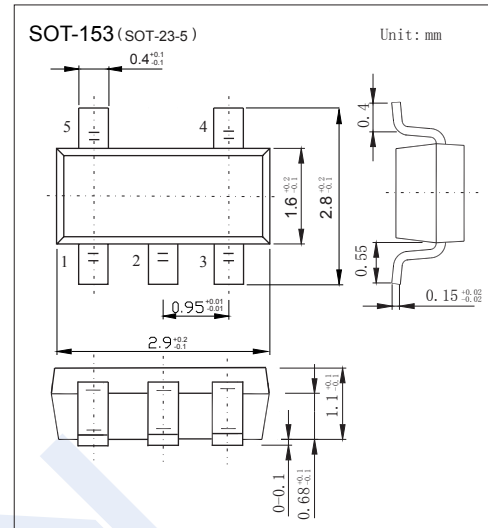
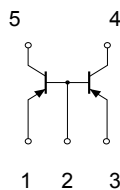


PNP Transistors

FMS4 (KMS4)

■ Features

- Collector Current Capability $I_C = -50\text{mA}$
- Collector Emitter Voltage $V_{CE0} = -120\text{V}$
- High breakdown voltage.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-120	V
Collector - Emitter Voltage	V_{CE0}	-120	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_C	-50	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100\ \mu\text{A}$, $I_E = 0$	-120			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -1\ \text{mA}$, $I_B = 0$	-120			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100\ \mu\text{A}$, $I_C = 0$	-5			
Collector-base cut-off current	I_{CB0}	$V_{CB} = -100\ \text{V}$, $I_E = 0$			-0.5	μA
Emitter cut-off current	I_{EB0}	$V_{EB} = -4\ \text{V}$, $I_C = 0$			-0.5	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10\ \text{mA}$, $I_B = -1\ \text{mA}$			-0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10\ \text{mA}$, $I_B = -1\ \text{mA}$			-1.2	
DC current gain	h_{FE}	$V_{CE} = -6\ \text{V}$, $I_C = -2\ \text{mA}$	180		820	
Transition frequency	f_T	$V_{CE} = -12\ \text{V}$, $I_E = 2\ \text{mA}$, $f = 100\ \text{MHz}$		140		MHz

■ Marking

Marking	S4
---------	----